

D CUMENT-IDENTIFIER: US 5034957 A
TITLE: Semiconductor laser device

DEPR:

Thus, in the Zn-doping of the p-type cladding layer, the diffusion of the Zn into the active layer, and thereby the threshold current, can be suppressed by setting the carrier concentration in the p-type cladding layer to be less than a half of the maximum value obtainable, which is $2.5 \times 10^{17} \text{ cm}^{-3}$.

CCOR:

372/45

CCXR:

372/46

	Type	Hit	S a r h Text	DBs	Time Stamp	Comments	Error D finiti n	Error
1	BRS	5915	diffusion with (suppress\$ or avoid\$)	USPAT	2002/01/07 11:40			0
2	BRS	104	(diffusion with (suppress\$ or avoid\$)) and 372/43-50.ccls.	USPAT	2002/01/07 15:25			0